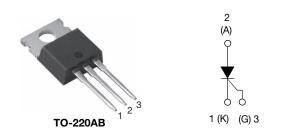
# VS-40TTS12PbF, VS-40TTS12-M3

Vishay Semiconductors

# Thyristor High Voltage, Phase Control SCR, 40 A



PRODUCT SUMMARY				
Package	TO-220AB			
Diode variation	Single SCR			
I <sub>T(AV)</sub>	25 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V			
V <sub>TM</sub>	1.6 V			
I <sub>GT</sub>	35 mA			
TJ	- 40 °C to 140 °C			

### FEATURES

- Designed and qualified according to JEDEC-JESD47
- 140 °C max. operating junction temperature
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **APPLICATIONS**

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

### DESCRIPTION

The VS-40TTS12... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 140 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	AMETER TEST CONDITIONS VALUES UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	25	٨				
I <sub>RMS</sub>		40	A				
V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V				
I <sub>TSM</sub>		350	А				
V <sub>T</sub>	T <sub>J</sub> = 25 °C	1.6	V				
dV/dt		500	V/µs				
dl/dt		150	A/µs				
TJ		- 40 to 140	°C				

VOLTAGE RATINGS					
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	TJ ℃		
VS-40TTS12PbF, VS-40TTS12-M3	1200	1200	- 25 to 140		

Revision: 26-Jul-13

Document Number: 94390

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# VS-40TTS12PbF, VS-40TTS12-M3

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS		
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° conduc	tion half sine wave	25			
Maximum RMS on-state current	I <sub>RMS</sub>			40	А		
Maximum peak, one-cycle	l	10 ms sine pulse, rated \	/ <sub>RRM</sub> applied	300	A		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no volt	age reapplied	350			
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated \	/ <sub>RRM</sub> applied	450	A <sup>2</sup> s		
	1-1	10 ms sine pulse, no volt	age reapplied	630			
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 to 10 ms, no volta	ige reapplied	6300	A²√s		
Maximum on-state voltage	V <sub>TM</sub>	80 A, T <sub>J</sub> = 25 °C		1.6	V		
Low level value of on-state slope resistance	r <sub>t</sub>	T <sub>J</sub> = 140 °C		11.4	mΩ		
Low level value of threshold voltage	V <sub>T(TO)</sub>	1j=140 C		0.96	V		
Maximum reverse and direct leakage	1 /1	T <sub>J</sub> = 25 °C	$V_{\rm e}$ = Dated $V_{\rm e}$ //	0.5			
current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 140 °C	$V_{R} = Rated V_{RRM} / V_{DRM}$	12			
Holding current	Ι <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		100	mA		
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		200			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$ , linear to 80	°C, $V_{DRM} = R_g - k = Open$	500	V/µs		
Maximum rate of rise of turned-on current	dl/dt			150	A/µs		

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>		8.0	W
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	А
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J$ = 25 °C	35	mA
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J$ = 25 °C	1.3	V
Maximum DC gate voltage not to trigger	V <sub>GD</sub>	Tr = 140 °C Verse = Poted volue	0.2	
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 140 °C, V <sub>DRM</sub> = Rated value	1.5	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 140 °C	4	μs
Typical turn-off time	t <sub>q</sub>	1j = 140 C	110	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 140	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	0.8		
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		60	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	oz.	
Mounting torque	minimum			6 (5)	kgf ⋅ cm	
Mounting torque	maximum			12 (10)	(lbf ⋅ in)	
Marking device			Case style TO-220AB	40TT	r\$12	

Revision: 26-Jul-13

Document Number: 94390

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#### Maximum Allowable Case Temperature (°C 140 RthJC (DC) = 0.8 °C/W 130 120 Conduction Angle 110 30° 100 -60 90 90 120 180° 80 70 0 5 10 15 20 25 30 Average On-state Current (A)

Fig. 1 - Current Rating Characteristics

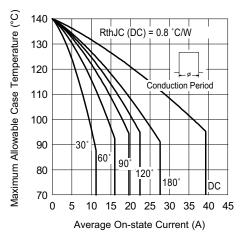


Fig. 2 - Current Rating Characteristics

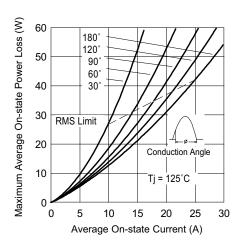


Fig. 3 - On-State Power Loss Characteristics

# VS-40TTS12PbF, VS-40TTS12-M3

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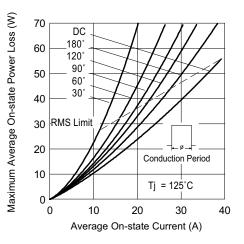
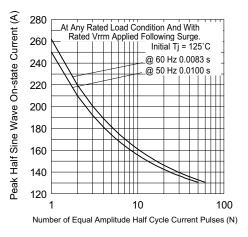


Fig. 4 - On-State Power Loss Characteristics



#### Fig. 5 - Maximum Non-Repetitive Surge Current

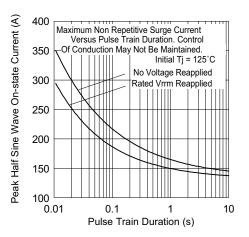


Fig. 6 - Maximum Non-Repetitive Surge Current

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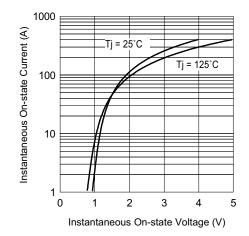
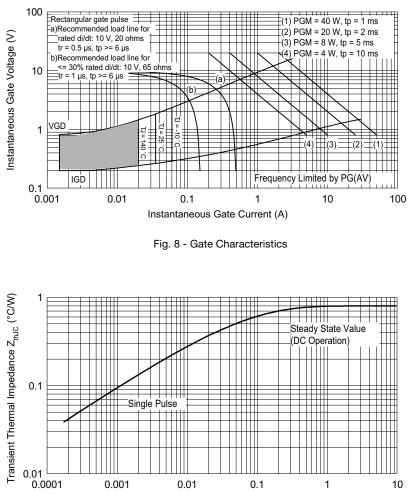
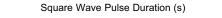
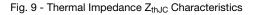


Fig. 7 - On-State Voltage Drop Characteristics







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# VS-40TTS12PbF, VS-40TTS12-M3

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### **ORDERING INFORMATION TABLE**

Device code	VS-	40	т	т	s	12	PbF
	(1)	(2)	(3)	(4)	(5)	(6)	(7)
	1	- Visł	nay Sem	niconduc	tors pro	duct	
	2	- Cur	rent rati	ng, RMS	S value		
	3	- Circ	uit conf	guratior	1:		
	_		Single t	hyristor			
	4		kage:				
			TO-220				
	5		e of silic Standar	on: d recov	orv rocti	fior	
	6			ng (12 =	•		
	F		ronmen	0 (		,	
				(Pb)-fre	e and R	oHS co	moliant
				en-free,			•

ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-40TTS12PbF	50	1000	Antistatic plastic tubes			
VS-40TTS12-M3	50	1000	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95222					
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028			

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**Vishay Semiconductors** 

**TO-220AB** 

### **DIMENSIONS** in millimeters and inches





.ead	assignments

**Diodes** 

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014 0.024		
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- <sup>(2)</sup> Lead dimension and finish uncontrolled in L1
- <sup>(3)</sup> Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left( 4\right) }$  Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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